74HC175-Q100; 74HCT175-Q100

Quad D-type flip-flop with reset; positive-edge trigger
Rev. 1 — 19 May 2014 Product of

Product data sheet

General description 1.

The 74HC175-Q100; 74HCT175-Q100 are quad positive edge-triggered D-type flip-flops with individual data inputs (Dn) and both Qn and Qn outputs. The common clock (CP) and master reset (MR) inputs load and reset all flip-flops simultaneously. The D-input that meets the set-up and hold time requirements on the LOW-to-HIGH clock transition is stored in the flip-flop and appears at the Q output. A LOW on MR causes the flip-flops and outputs to be reset LOW.

The device is useful for applications where both the true and complement outputs are required and the clock and master reset are common to all storage elements.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. **Features and benefits**

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Input levels:
 - ◆ For 74HC175-Q100: CMOS level
 - ◆ For 74HCT175-Q100: TTL level
- Four edge-triggered D-type flip-flops
- Asynchronous master reset
- Complies with JEDEC standard no. 7A
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

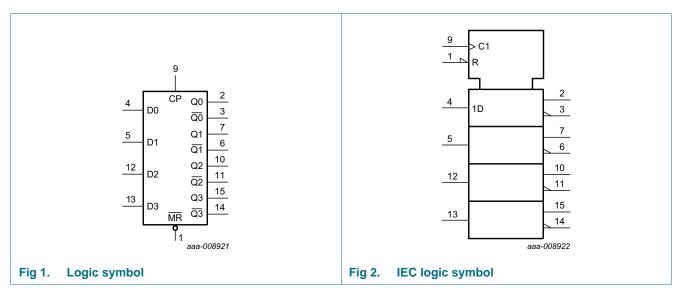


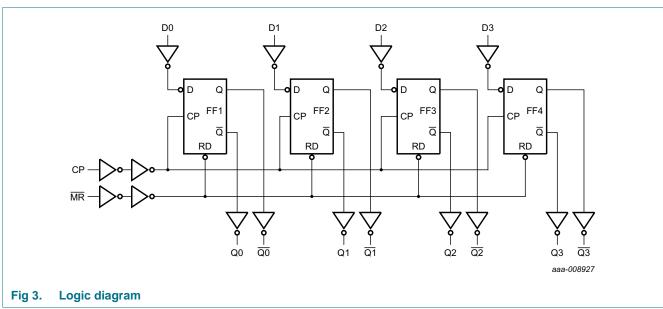
3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range Name Description Ve								
74HC175D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1					
74HCT175D-Q100			3.9 mm						
74HC175PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads;	SOT403-1					
74HCT175PW-Q100			body width 4.4 mm						

4. Functional diagram

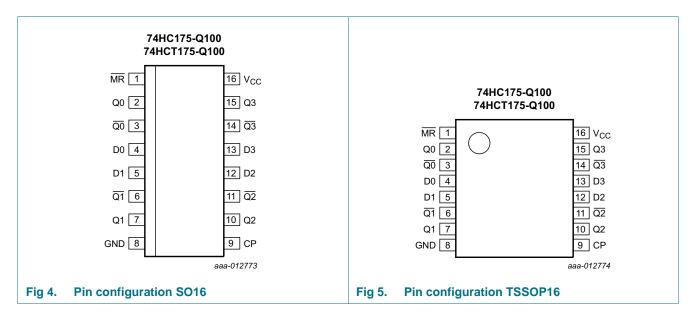




74HC_HCT175_Q100

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description	
MR	1	asynchronous master reset input (active LOW)	
Q0 to Q3	2, 7, 10, 15	flip-flop output	
Q0 to Q3	3, 6, 11, 14	complementary flip-flop output	
D0 to D3	4, 5, 12, 13	data input	
GND	8	ground (0 V)	
СР	9	clock input (LOW-to-HIGH edge-triggered)	
V _{CC}	16	positive supply voltage	

6. Functional description

Table 3. Function table[1]

Operating modes	Inputs			Outputs		
	MR	СР	Qn	Qn		
reset (clear)	L	X	X	L	Н	
load "1"	Н	\uparrow	h	Н	L	
load "0"	Н	\uparrow	I	L	Н	

[1] H = HIGH voltage level;

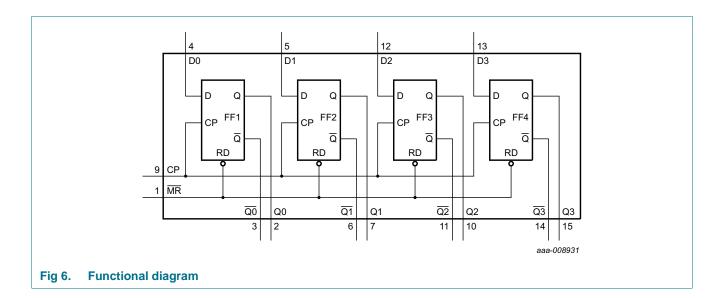
h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;

X = don't care;

↑ = LOW-to-HIGH clock transition.



7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$ [1]	-	500	mW

^[1] For SO16 package: above 70 °C the value of P_{tot} derates linearly with 8 mW/K. For TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC1	74HC175-Q100			74HCT175-Q100		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC17	5-Q100									
V _{IH}	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	٧
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	٧
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	٧
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}						1		
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_O = -20 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_O = -20 \mu A$; $V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	٧
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}						1		
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
cc	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μА
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	75-Q100									
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{ОН}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 5.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1	-	±1	μА

74HC_HCT175_Q100

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V								
		Dn input	-	40	144	-	180	-	196	μΑ
		CP input	-	60	216	-	270	-	294	μΑ
		MR input	-	100	360	-	450	-	490	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 10

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC17	5-Q100									
t _{pd}	propagation delay	CP to Qn, Qn; [1] see Figure 7								
		V _{CC} = 2.0 V	-	55	175	-	220	-	265	ns
		V _{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	17	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	16	30	-	37	-	45	ns
t _{PHL}	HIGH to LOW propagation	MR to Qn, Qn; see Figure 9								
	delay	V _{CC} = 2.0 V	-	50	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	18	30	-	38	-	45	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _t	transition time	Qn output; see Figure 7 [2]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

 Table 7.
 Dynamic characteristics ...continued

GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see Figure 10

Symbol	Parameter	er Conditions		25 °C		–40 °C t	o +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
t _W	pulse width	CP input HIGH or LOW; see Figure 7								
		V _{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	6	-	17	-	20	-	ns
		MR input LOW; see Figure 9								
		V _{CC} = 2.0 V	80	19	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	7	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	6	-	17	-	20	-	ns
t _{rec}	recovery time	MR to CP; see Figure 9								
		V _{CC} = 2.0 V	5	-33	-	5	-	5	-	ns
		V _{CC} = 4.5 V	5	-12	-	5	-	5	-	ns
		V _{CC} = 6.0 V	5	-10	-	5	-	5	-	ns
t _{su}	set-up time	Dn to CP; see Figure 7								
		V _{CC} = 2.0 V	80	3	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	1	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	1	-	17	-	20	-	ns
t _h	hold time	Dn to CP; see Figure 7								
		V _{CC} = 2.0 V	25	2	-	30	-	40	-	ns
		V _{CC} = 4.5 V	5	0	-	6	-	8	-	ns
		V _{CC} = 6.0 V	4	0	-	5	-	7	-	ns
f _{max}	maximum	CP input; see Figure 7								
	frequency	V _{CC} = 2.0 V	6	25	-	4.8	-	4	-	MHz
		V _{CC} = 4.5 V	30	75	-	24	-	20	-	MHz
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	83	-	-	-	-	-	MHz
		V _{CC} = 6.0 V	35	89	-	28	-	24	-	MHz
C _{PD}	power dissipation capacitance	per package; $V_I = GND \text{ to } V_{CC}$	-	32	-	-	-	-	-	pF
74HCT17	-			1		1	1			1
t _{pd}	propagation delay	CP to Qn, Qn; [1] see Figure 7								
		V _{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	16	-	-	-	-	-	ns

 Table 7.
 Dynamic characteristics ...continued

GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 10

Symbol	Parameter	Conditions		25 °C	;	-40 °C 1	to +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	Ī
t _{PHL}	HIGH to LOW	MR to Qn; see Figure 9								
	propagation	V _{CC} = 4.5 V	-	22	38	-	48	-	57	ns
	delay	$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	19	-	-	-	-	-	ns
		MR to Qn; see Figure 9								
		V _{CC} = 4.5 V	-	19	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	16	-	-	-	-	-	ns
t _t	transition time	Qn output; see Figure 7	[
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t _W	pulse width	CP input; see Figure 7	·	,						
		V _{CC} = 4.5 V	20	12	-	25	-	30	-	ns
	MR input LOW;									
		see Figure 9								
		V _{CC} = 4.5 V	20	11	-	25	-	30	-	ns
t _{rec}	recovery time	MR to CP; see Figure 9								
		V _{CC} = 4.5 V	5	-10	-	5	-	5	-	ns
t _{su}	set-up time	Dn to CP; see Figure 7					_			
		$V_{CC} = 4.5 \text{ V}$	16	5	-	20	-	24	-	ns
t _h	hold time	Dn to CP; see Figure 7								
		V _{CC} = 4.5 V	5	0	-	5	-	5	-	ns
f _{max}	maximum	CP input; see Figure 7								
	frequency	V _{CC} = 4.5 V	25	49	-	20	-	17	-	MHz
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$	-	54	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	-	34	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

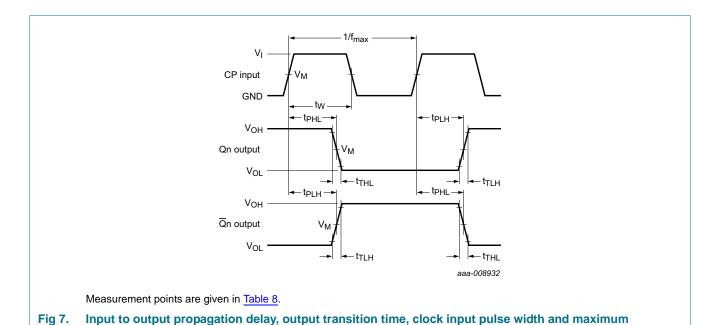
 $\Sigma (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs};$

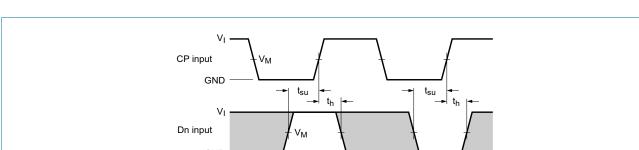
 C_L = output load capacitance in pF;

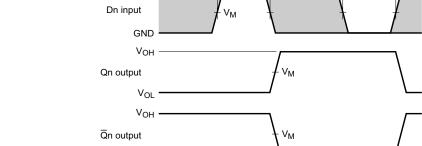
 V_{CC} = supply voltage in V.

11. Waveforms

frequency





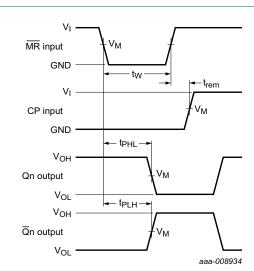


Measurement points are given in Table 8.

 V_{OL}

Fig 8. Data set-up and hold times for data input

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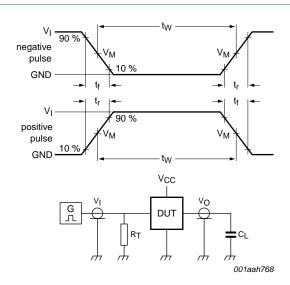


Measurement points are given in Table 8.

Fig 9. Master reset to output propagation delays, master reset pulse width and master reset to clock recovery time

Table 8. Measurement points

Туре	Input		Output
	VI	V _M	V _M
74HC175-Q100	V _{CC}	0.5V _{CC}	0.5V _{CC}
74HCT175-Q100	3 V	1.3 V	1.3 V



Test data is given in Table 9.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

Fig 10. Test circuit for measuring switching times

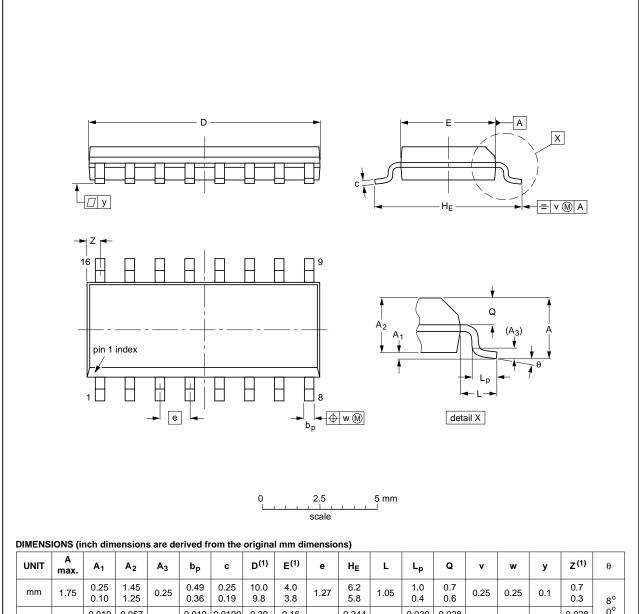
Table 9. Test data

Туре	Input		Load		Test
	V _I	t _r , t _f	C _L	R _L	
74HC175-Q100	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	t _{PLH} , t _{PHL}
74HCT175-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	t _{PLH} , t _{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	l	0.0100 0.0075		0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

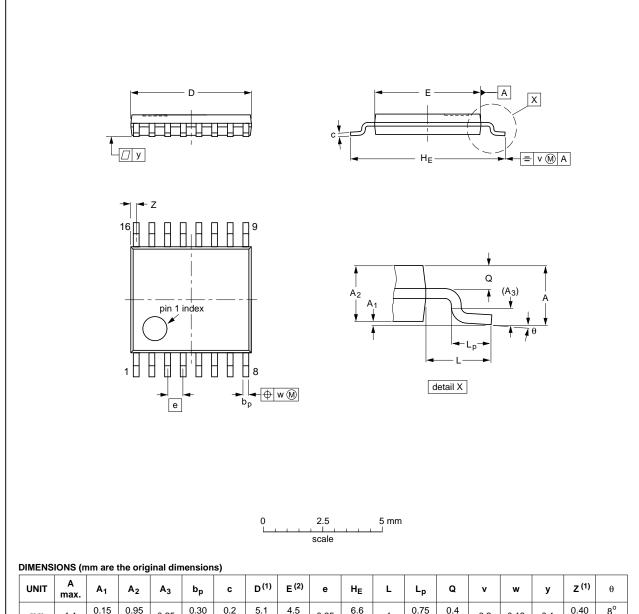
Fig 11. Package outline SOT109-1 (SO16)

74HC_HCT175_Q100

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT403-1		MO-153				99-12-27 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

74HC_HCT175_Q100

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT175_Q100 v.1	20140519	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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Quad D-type flip-flop with reset; positive-edge trigger

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